

## BJT Applications

**Topics Covered from Module 4:** BJT as an amplifier, BJT as a switch, Transistor switch circuit to switch ON/OFF an LED and a lamp in a power circuit using a relay.

### BJT as an Amplifier

Amplification is the process of linearly increasing the amplitude of an electrical signal. It is one of the major properties of a bipolar junction transistor (BJT).

A BJT is a current controlled device. It amplifies current because the collector current is equal to the base current multiplied by the current gain,  $\beta$ . The base current in a transistor is very small compared to the collector and emitter currents. Because of this, the collector current is approximately equal to the emitter current.

Fig. 1 shows a basic transistor amplifier circuit. An ac voltage,  $V_s$ , is superimposed on the dc bias voltage  $V_{BB}$  by capacitive coupling as shown. The dc bias voltage  $V_{CC}$  is connected to the collector through the collector resistor,  $R_C$ .

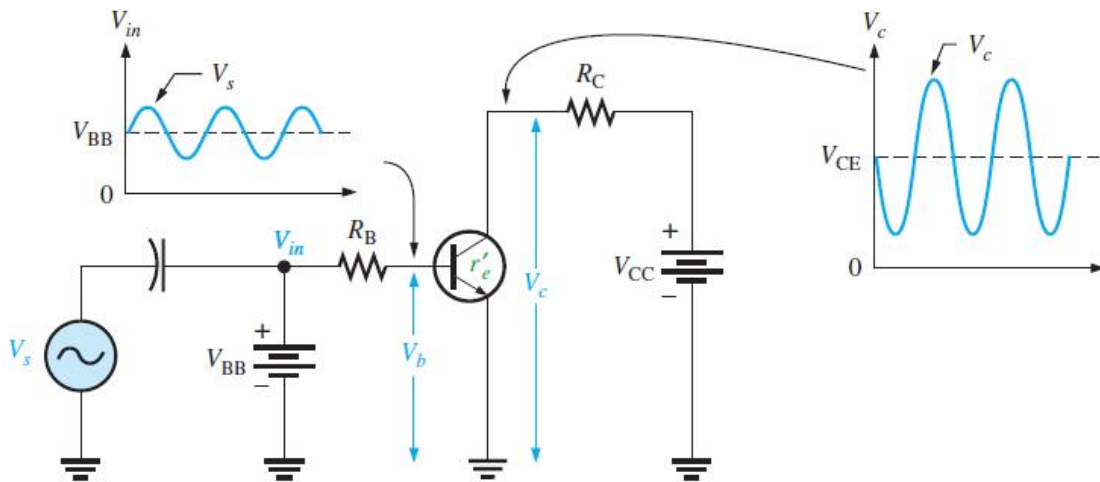


Fig. 1 Basic transistor amplifier circuit

The ac input voltage produces an ac base current  $I_b$ , which results in a much larger ac collector current  $I_c$ . The ac collector current  $I_c$  produces an ac voltage across  $R_C$ , thus producing an amplified, but inverted, reproduction of the ac input voltage as shown in Fig. 1.

The forward-biased base-emitter junction presents a very low resistance to the ac signal. This internal ac emitter resistance is designated  $r'_e$  and appears in series with  $R_B$ . The ac base voltage is

$$V_b = I_e r'_e$$

The ac collector voltage,  $V_c$ , equals the ac voltage drop across  $R_C$ .

$$V_c = I_c R_C$$

Since  $I_c \cong I_e$ , the ac collector voltage is

$$V_c \cong I_e R_C$$

$V_b$  can be considered the transistor ac input voltage where  $V_b = V_s - I_b R_B$ .  $V_c$  can be considered the transistor ac output voltage.

Since *voltage gain* is defined as the ratio of the output voltage to the input voltage, the ratio of  $V_c$  to  $V_b$  is the ac voltage gain,  $A_v$ , of the transistor.

$$A_v = \frac{V_c}{V_b}$$

Substituting  $I_e R_C$  for  $V_c$  and  $I_e r'_e$  for  $V_b$  yields

$$A_v = \frac{V_c}{V_b} \cong \frac{I_e R_C}{I_e r'_e}$$

Therefore,

$$A_v \cong \frac{R_C}{r'_e}$$

This equation shows that the transistor in Fig. 1 provides amplification in the form of voltage gain, which is dependent on the values of  $R_C$  and  $r'_e$ . Since  $R_C$  is always considerably larger in value than  $r'_e$ , the output voltage for this configuration is greater than the input voltage.

## BJT as a Switch

The second major application area of BJT is switching applications. When used as an electronic switch, a BJT is normally operated alternately in cutoff and saturation. Many digital circuits use the BJT as a switch.

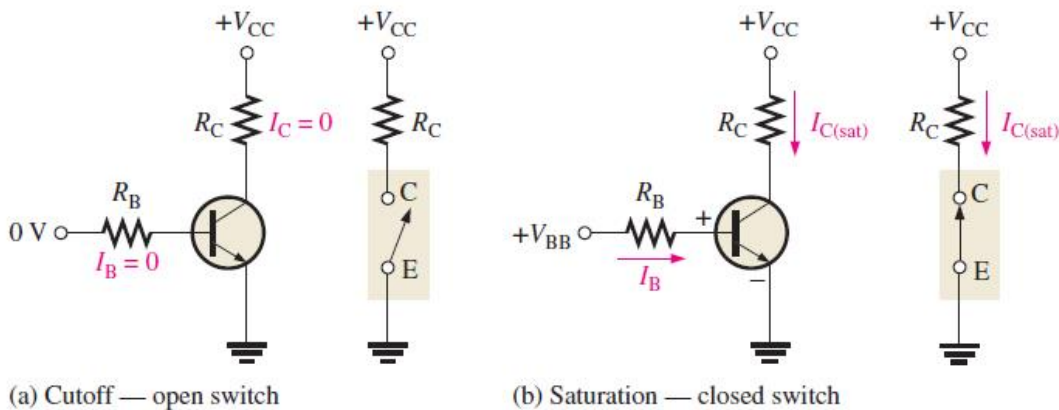


Fig. 2 Switching action of an ideal transistor

Fig. 2 illustrates the basic operation of a BJT as a switching device.

In Fig. 2 (a), the transistor is in the cutoff region because the base-emitter junction is not forward-biased. In this condition, there is, ideally, an open between collector and emitter, as indicated by the switch equivalent.

In Fig. 2 (b), the transistor is in the saturation region because the base-emitter junction and the base-collector junction are forward-biased and the base current is made large enough to cause the collector current to reach its saturation value. In this condition, there is, ideally, a short between collector and emitter, as indicated by the switch equivalent. Actually, a small voltage drop across the transistor of up to a few tenths of a volt normally occurs, which is the saturation voltage,  $V_{CE(sat)}$ .

## Conditions in Cutoff

A transistor is in the cutoff region when the base-emitter junction is not forward-biased. Neglecting leakage current, all of the currents are zero, and  $V_{CE}$  is equal to  $V_{CC}$ .

$$V_{CE(cutoff)} = V_{CC}$$

## Conditions in Saturation

When the base-emitter junction is forward-biased and there is enough base current to produce a maximum collector current, the transistor is saturated. The formula for collector saturation current is

$$I_{C(sat)} = \frac{V_{CC} - V_{CE(sat)}}{R_C}$$

Since  $V_{CE(sat)}$  is very small compared to  $V_{CC}$ , it can usually be neglected.

The minimum value of base current needed to produce saturation is

$$I_{B(min)} = \frac{I_{C(sat)}}{\beta_{DC}}$$

Normally,  $I_B$  should be significantly greater than  $I_{B(min)}$  to ensure that the transistor is saturated.

## A Simple Application of a Transistor Switch

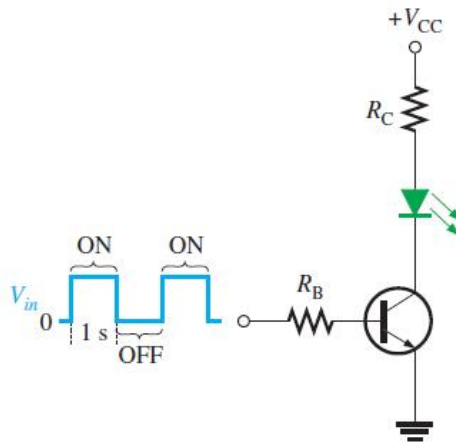


Fig. 3 A transistor used to switch an LED on and off

The transistor in Fig. 3 is used as a switch to turn the LED on and off.

For example, a square wave input voltage with a period of 2 s is applied to the input as indicated. When the square wave is at 0 V, the transistor is in cutoff; and since there is no collector current, the LED does not emit light. When the square wave goes to its high level, the transistor saturates. This forward-biases the LED, and the resulting collector current through the LED causes it to emit light. Thus, the LED is on for 1 second and off for 1 second.

## Numerical Examples

1. What is the voltage gain of a transistor amplifier that has an output of 5 V rms and an input of 250 mV rms?

*Solution:*

Given  $V_{in} = 250 \text{ mV}$ ,  $V_{out} = 5 \text{ V}$

We know that,

The voltage gain

$$A_v = \frac{V_{out}}{V_{in}}$$

$$= \frac{5 \text{ V}}{250 \times 10^{-3} \text{ V}}$$

$$A_v = \underline{\underline{20}}$$

2. In a transistor amplifier circuit, determine the voltage gain and the ac output voltage if  $V_b = 100 \text{ mV}$ ,  $R_c = 1 \text{ k}\Omega$  and  $r'_e = 50 \Omega$ .

*Solution:*

Given.  $V_b = 100 \text{ mV} = 100 \times 10^{-3} \text{ V}$   
 $R_c = 1 \text{ k}\Omega = 1 \times 10^3 \Omega$ ,  $r'_e = 50 \Omega$

We know that,

The voltage gain

$$A_v = \frac{V_c}{V_b}$$

$$A_v = \frac{R_c}{r'_e}$$

$$= \frac{1 \times 10^3}{50}$$

$$\boxed{A_v = 20}$$

Since  $A_v = \frac{V_c}{V_b}$ ,

The ac output voltage

$$V_c = A_v V_b$$

$$= 20 \times 100 \times 10^{-3} \text{ V}$$

$$V_c = 2 \text{ V}$$

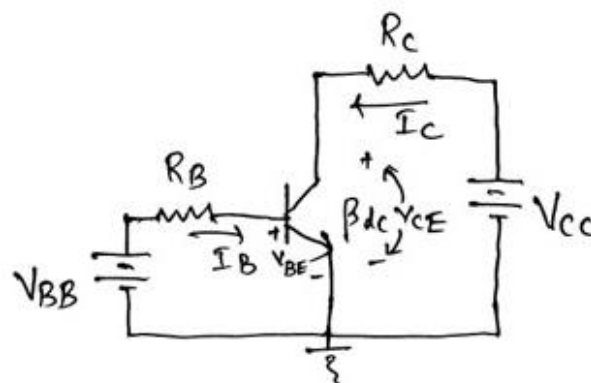
3. Determine the value of the collector resistor in an npn transistor amplifier with  $\beta_{dc} = 250$ ,  $V_{BB} = 2.5 \text{ V}$ ,  $V_{CC} = 9 \text{ V}$ ,  $V_{CE} = 4 \text{ V}$  and  $R_B = 100 \text{ k}\Omega$ .

Solution:

Given  $\beta_{dc} = 250$ ,  $V_{BB} = 2.5 \text{ V}$ ,  $V_{CC} = 9 \text{ V}$ ,

$V_{CE} = 4 \text{ V}$ ,  $R_B = 100 \text{ k}\Omega$

We have the circuit of an npn transistor amplifier as



from the circuit,

$$V_{BB} = I_B R_B + V_{BE}$$

$$I_B R_B = V_{BB} - V_{BE}$$

$$I_B = \frac{V_{BB} - V_{BE}}{R_B}$$

Consider Si transistor,

Since Base-Emitter junction is forward biased,  $V_{BE} = 0.7 \text{ V}$

$$\therefore I_B = \frac{2.5 - 0.7}{100 \times 10^3}$$

$$I_B = \underline{\underline{18 \mu A}}$$

We know that

$$I_C = \beta_{dc} I_B$$

$$\therefore I_C = 250 \times 18 \times 10^{-6}$$

$$I_C = \underline{\underline{4.5 \text{ mA}}}$$

From the circuit,

$$V_{CC} = I_C R_C + V_{CE}$$

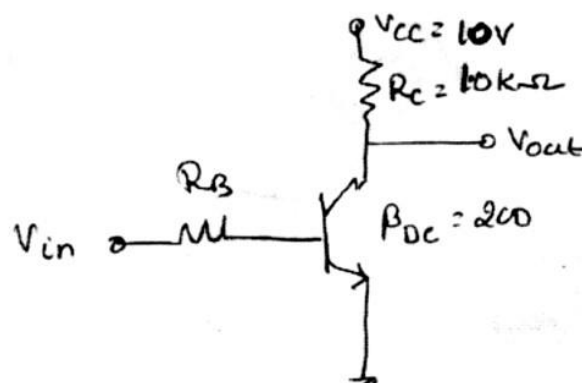
$$I_C R_C = V_{CC} - V_{CE}$$

$$R_C = \frac{V_{CC} - V_{CE}}{I_C}$$

$$R_C = \frac{9 - 4}{4.5 \times 10^{-3}}$$

$$R_C = \underline{\underline{1.11 \text{ k}\Omega}}$$

4. The transistor in common emitter configuration is shown in figure, with  $R_C = 1.0 \text{ k}\Omega$  and  $\beta_{dc} = 200$ . Determine (i)  $V_{CE}$  at  $V_{in} = 0$  (ii)  $I_{B(\text{min})}$  to saturate the collector current (iii)  $R_{B(\text{max})}$  when  $V_{in} = 5 \text{ V}$ .  $V_{CE(\text{sat})}$  can be neglected.



Solution:

i) When  $V_{in} = 0V$ , the transistor is in cutoff  
(acts as an open switch)

We know that,

$$V_{CE(\text{cutoff})} = V_{CC} = \underline{\underline{10V}}$$

ii)

$$I_{C(\text{sat})} = \frac{V_{CC} - V_{CE(\text{sat})}}{R_C}$$

Since  $V_{CE(\text{sat})}$  is neglected,

$$\begin{aligned} I_{C(\text{sat})} &= \frac{V_{CC}}{R_C} \\ &= \frac{10}{1 \times 10^{-3}} = \underline{\underline{10mA}} \end{aligned}$$

Then,

$$\begin{aligned} I_{B(\text{min})} &= \frac{I_{C(\text{sat})}}{\beta_{dc}} \\ &= \frac{10 \times 10^{-3}}{200} = \underline{\underline{50\mu A}} \end{aligned}$$

iii) The voltage across  $R_B$  is

$$V_{RB} = V_{in} - V_{BE}$$

Assume  $V_{BE} = 0.7V$  (ON state)

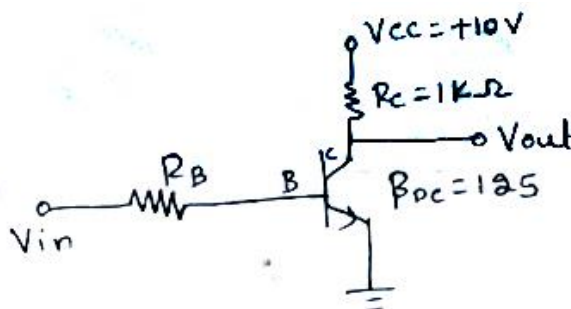
$$V_{RB} = 5 - 0.7 = 4.3V$$

Then

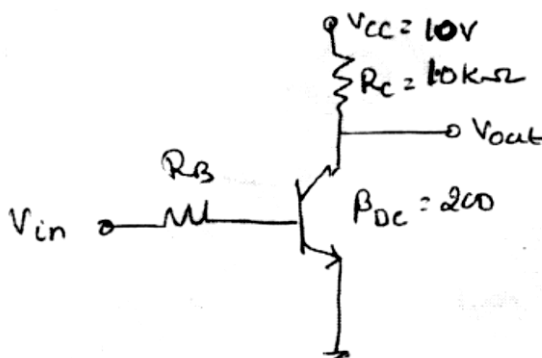
$$\begin{aligned} R_{B(\text{max})} &= \frac{V_{RB}}{I_{B(\text{min})}} \\ &= \frac{4.3}{50 \times 10^{-6}} = \underline{\underline{86k\Omega}} \end{aligned}$$

## Questions

1. What is an amplifier? Explain the operation of transistor amplifier circuit. (MQP '18 - 8M)
2. With neat circuit diagram, explain how transistor is used as a voltage amplifier. Derive an equation for voltage gain  $A_v$ . (Sep '20 - 8M, Jan '20 - 8M, Jul '19 - 6M, Jan '19 - 8M)
3. Briefly explain how a transistor is used as an electronic switch. (MQP '18 - 6M)
4. Explain the operation of BJT (transistor) as an amplifier and as a switch. (MQP '18 - 10M)
5. With a neat circuit diagram, explain how transistor can be used to switch an LED ON/OFF and give the necessary equations. (Jan '19 - 8M)
6. Determine the value of the collector resistor in an npn transistor amplifier with  $\beta_{dc} = 250$ ,  $V_{BB} = 2.5$  V,  $V_{CC} = 9$  V,  $V_{CE} = 4$  V and  $R_B = 100$  k $\Omega$ .
7. In a transistor amplifier circuit, determine the voltage gain and the ac output voltage if  $V_b = 100$  mV,  $R_C = 1$  k $\Omega$  and  $r'_e = 50$   $\Omega$ .
8. The transistor in CE configuration is shown in figure, with  $R_C = 1$  k $\Omega$  and  $\beta_{dc} = 125$ . Determine (i)  $V_{CE}$  at  $V_{in} = 0$  V (ii)  $I_{B(min)}$  to saturate the collector current (iii)  $R_{B(max)}$  when  $V_{in} = 8$  V.  $V_{CE(sat)}$  can be neglected. (Jan '20 - 4M)



9. The transistor in common emitter configuration is shown in figure, with  $R_C = 1.0$  k $\Omega$  and  $\beta_{dc} = 200$ . Determine (i)  $V_{CE}$  at  $V_{in} = 0$  (ii)  $I_{B(min)}$  to saturate the collector current (iii)  $R_{B(max)}$  when  $V_{in} = 5$  V.  $V_{CE(sat)}$  can be neglected. (Jan '19 - 4M)



## References

1. Thomas L. Floyd, "**Electronic Devices**", Pearson Education, Ninth Edition, 2012.



2. David A. Bell, "**Electronic Devices and Circuits**", Oxford University Press, 5th Edition, 2008.
3. D.P. Kothari, I. J. Nagrath, "**Basic Electronics**", McGraw Hill Education (India) Private Limited, Second Edition, 2014.